N-CHANNEL IG-MOS-FET

Symmetrical depletion type field-effect transistor in a TO-72 metal envelope with the substrate connected to the case. It is intended for chopper and other special switching applications, e.g. timing circuits, multiplex circuits, etc. The features are a very low drain-source 'on' resistance, a very high drain-source 'off' resistance and low feedback capacitances.

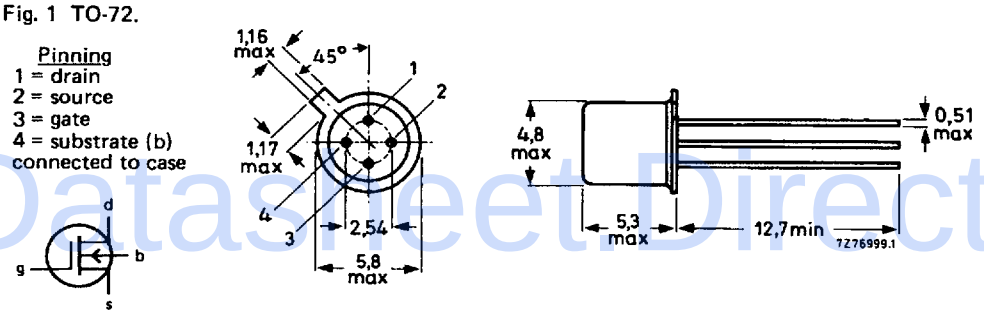
QUICK REFERENCE DATA

Drain-source resistance (on) at f = 1 kHz			
V_{DS} = 0; V_{GS} = 5 V; V_{BS} = 0	$R_{ds\ on}$	max.	50 Ω
Drain-source resistance (off)			
V_{DS} = 10 V; $-V_{GS}$ = 5 V; V_{BS} = 0	$R_{DS\ off}$	min.	10 GΩ
Feedback capacitance at f = 1 MHz			
$-V_{GS}$ = 5 V; V_{DS} = 0; I_B = 0	C_{rs}	typ.	0.5 pF
$-V_{GD}$ = 5 V; V_{SD} = 0; I_B = 0	C_{rd}	typ.	0.5 pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 TO-72.



Accessories: 56246 (distance disc).

Note

To safeguard the gates against damage due to accumulation of static charge during transport or handling, the leads are encircled by a ring of conductive rubber which should be removed just after the transistor is soldered into the circuit.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-substrate voltage	V_{DB}	max.	30 V
Source-substrate voltage	V_{SB}	max.	30 V
Gate-substrate voltage (continuous)	V_{GB}	max. min.	10 V −10 V
Repetitive peak gate to all other terminals voltage $V_{SB} = V_{DB} = 0$; $f > 100$ Hz	V_{G-N}	max. min.	15 V −15 V
Non-repetitive peak gate to all other terminals voltage $V_{SB} = V_{DB} = 0$; $t < 10$ ms	V_{G-N}	max. min.	50 V −50 V
Drain current (DC)	I_D	max.	25 mA
Drain current (peak value) $t_p = 20$ ms; $\delta = 0.1$	I_{DM}	max.	50 mA
Source current (peak value) $t_p = 20$ ms; $\delta = 0.1$	I_{SM}	max.	50 mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	200 mW
Storage temperature range	T_{stg}		−65 to + 125 °C
Junction temperature	T_j	max.	125 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j-a}$	=	500 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain cut-off currents; V_{BS} = 0				
V_{DS} = 10 V; $-V_{GS}$ = 5 V	I_{DSX}	<	1	nA
V_{DS} = 10 V; $-V_{GS}$ = 5 V; T_j = 125 °C	I_{DSX}	<	1	µA
Source cut-off currents; V_{BD} = 0				
V_{SD} = 10 V; $-V_{GD}$ = 5 V	I_{SDX}	<	1	nA
V_{SD} = 10 V; $-V_{GD}$ = 5 V; T_j = 125 °C	I_{SDX}	<	1	µA
Gate currents; V_{BS} = 0				
$-V_{GS}$ = 10 V; V_{DS} = 0	$-I_{GSS}$	<	10	pA
V_{GS} = 10 V; V_{DS} = 0	I_{GSS}	<	10	pA
$-V_{GS}$ = 10 V; V_{DS} = 0; T_j = 125 °C	$-I_{GSS}$	<	200	pA
V_{GS} = 10 V; V_{DS} = 0; T_j = 125 °C	I_{GSS}	<	200	pA
Bulk currents; V_{GB} = 0				
$-V_{BD}$ = 30 V; I_S = 0	$-I_{BDO}$	<	10	µA
$-V_{BS}$ = 30 V; I_D = 0	$-I_{BSO}$	<	10	µA
Drain-source resistance (on) at f = 1 kHz; V_{BS} = 0				
V_{GS} = 0 ; V_{DS} = 0	$R_{ds\ on}$	<	100	Ω
V_{GS} = 0 ; V_{DS} = 0; T_j = 125 °C	$R_{ds\ on}$	<	150	Ω
$+V_{GS}$ = 5 V; V_{DS} = 0	$R_{ds\ on}$	<	50	Ω
Drain-source resistance (off)				
$-V_{GS}$ = 5 V; V_{DS} = 10 V; V_{BS} = 0	$R_{DS\ off}$	>	10	GΩ
Feedback capacitances at f = 1 MHz				
$-V_{GS}$ = 5 V; V_{DS} = 0; I_B = 0	C_{rs}	typ.	0.5	pF
$-V_{GD}$ = 5 V; V_{SD} = 0; I_B = 0	C_{rd}	typ.	0.5	pF
Gate to all other terminals capacitance at f = 1 MHz				
$-V_{GB}$ = 5 V; V_{SB} = V_{DB} = 0	C_{g-n}	<	6	pF